

wafer to change the conductivity type of a section of the first partial layer and a section of the second partial layer, whereby a second layer is formed; and

depositing metallic coatings on the top surface and the bottom surface of the wafer; and

separating the wafer along the trenches into individual chips, such that each chip has at least one trench in its interior.

12. (New) The method according to claim 11, further comprising the step of introducing the trenches by sawing.

13. (New) The method according to claim 11, further comprising the step of introducing the trenches by etching.--

Remarks

This Preliminary Amendment cancels original claims 1-7 and substitute claims 1-3 presented in the underlying PCT Application No. PCT/DE00/02235, and adds new claims 8-13. The new claims do not add new matter to the application, but do conform the claims to U.S. Patent and Trademark Office rules.

The amendments to the specification and abstract are to conform the specification and abstract to U.S. Patent and Trademark Office rules. The amendments to the specification and abstract do not introduce new matter into the application.

The underlying PCT application includes a Search Report dated December 5, 2000, and an International Preliminary Examination Report dated October 4, 2001, copies of which are submitted herewith. English translations of the Search Report and the International Preliminary Examination Report are also submitted herewith.

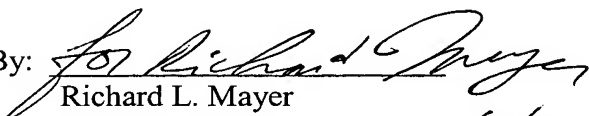
Applicants assert that the present invention is new, non-obvious, and useful. Consideration and allowance of the claims are requested.

Respectfully submitted,


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